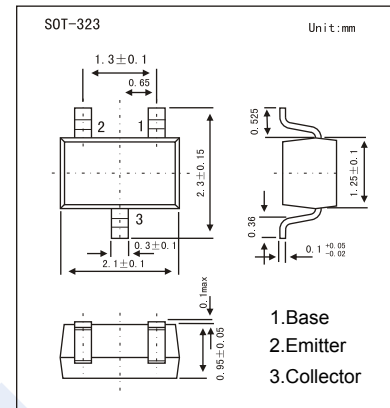


PNP Transistors

2SA1586

■ Features

- High DC Current Gain
- High Voltage and High Current.
- Complementary to 2SC4116
- Small Package



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-50	V
Collector - Emitter Voltage	V _{CEO}	-50	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-150	mA
Collector Power Dissipation	P _C	100	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	1250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E = 0	-50			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B = 0	-50			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5 V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100 mA, I _B = -10 mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -100 mA, I _B = -10 mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	70		400	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz			7	pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -1mA	80			MHz

■ Classification of h_{FE}

Type	2SA1586-O	2SA1586-Y	2SA1586-G
Range	70-140	120-240	200-400
Marking	SO	SY	SG

PNP Transistors

2SA1586

■ Typical Characteristics

